

ISL71010B50

Ultra Low Noise, 5V Precision Voltage Reference

Description

The **ISL71010B50** is an ultra low noise, high DC accuracy precision voltage reference, with a wide input voltage range from 7.0V to 30V. The ISL71010B50 uses the dielectrically isolated PR40 process to achieve $4.2\mu\text{V}_{\text{P-P}}$ noise at 0.1Hz to 10Hz with an initial voltage accuracy of $\pm 0.05\%$.

The ISL71010B50 offers a 5.0V output voltage with 10ppm/°C temperature coefficient and also provides excellent line and load regulation. The device is offered in an 8 Ld SOIC package.

The ISL71010B50 is ideal for high-end instrumentation, data acquisition, and processing applications requiring high DC precision where low noise performance is critical.

Applications

- Low Earth Orbit (LEO)
- High altitude avionics
- Precision instruments
- Data acquisition systems for space applications
- Strain and pressure gauges for space applications
- Active sources for sensors

Features

- Qualified to Renesas Rad Tolerant Screening and QCI Flow ([R34TB0004EU](#))
- Reference output voltage: $5.0\text{V} \pm 0.05\%$
- Accuracy over temperature/radiation: $\pm 0.15\%$
- Output voltage noise: $4.2\mu\text{V}_{\text{P-P}}$ typical (0.1Hz to 10Hz)
- Supply current: 930μA (typical)
- Temperature coefficient: 10ppm/°C (maximum)
- Output current capability: 20mA
- Line regulation: 20ppm/V (maximum)
- Load regulation: 17ppm/mA (maximum)
- NiPdAu-Ag lead finish (Sn Free)
- Dielectrically isolated PR40 process
- Operating temperature range: -55°C to $+125^\circ\text{C}$
- Passes NASA Low Outgassing Specifications
- TID Radiation Lot Acceptance Testing (RLAT) (LDR: $\leq 10\text{mrad}(\text{Si})/\text{s}$)
 - ISL71010BM30B50Z: 30krad(Si)
 - ISL71010BM50B50Z: 50krad(Si)
- SEE Characterization
 - No DSEE for $V_{\text{IN}} = 39\text{V}$ at $43\text{MeV}\cdot\text{cm}^2/\text{mg}$
 - V_{OUT} SET shorter than 160μs and $-300\text{mV} \leq \Delta V_{\text{OUT}} \leq 500\text{mV}$ at $28\text{MeV}\cdot\text{cm}^2/\text{mg}$

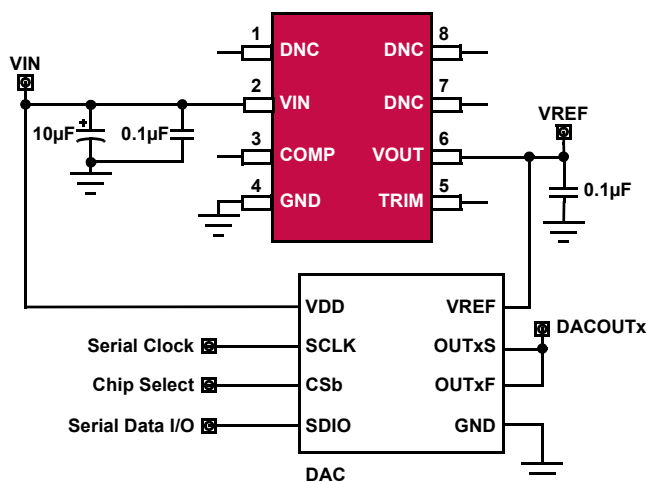


Figure 1. ISL71010B50 Typical Application Diagram

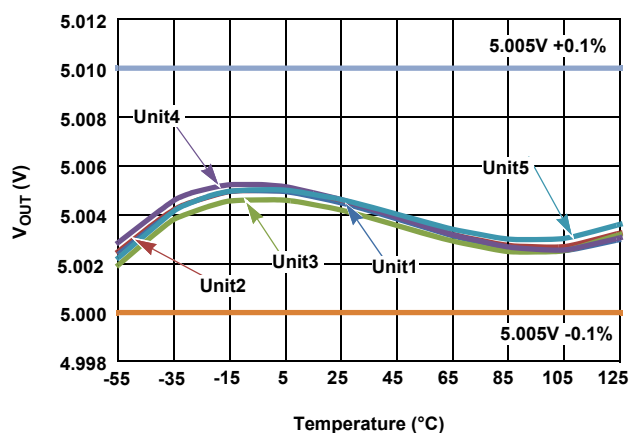


Figure 2. V_{OUT} vs Temperature

Contents

1. Overview	3
1.1 Functional Block Diagram	3
2. Pin Information	4
2.1 Pin Assignments	4
2.2 Pin Descriptions	4
3. Specifications	5
3.1 Absolute Maximum Ratings	5
3.2 Recommended Operating Conditions	5
3.3 Thermal Information	5
3.4 Outgas Testing	5
3.5 Electrical Specifications	6
4. Typical Performance Curves	7
5. Applications Information	12
5.1 Bandgap Precision Reference	12
5.2 Board Mounting Considerations	12
5.3 Board Assembly Considerations	12
5.4 Noise Performance and Reduction	12
5.5 Turn-On Time	12
5.6 Specifying Temperature Coefficient (Box Method)	12
5.7 Output Voltage Adjustment	12
5.8 Output Stage	13
5.9 Use of COMP Capacitors	13
6. Radiation Tolerance	13
6.1 Total Ionizing Dose (TID) Testing	13
6.1.1 Introduction	13
6.1.2 Results	14
6.1.3 Data Plots	14
6.1.4 Conclusion	15
6.2 Single Event Effects Testing	16
6.2.1 Introduction	16
6.2.2 SEE Test Setup	16
6.2.3 SEB Testing Results	16
6.2.4 Single Event Transient (SET) Testing	17
7. Conclusion	18
8. Package Outline Drawing	19
9. Ordering Information	19
10. Revision History	19

1. Overview

1.1 Functional Block Diagram

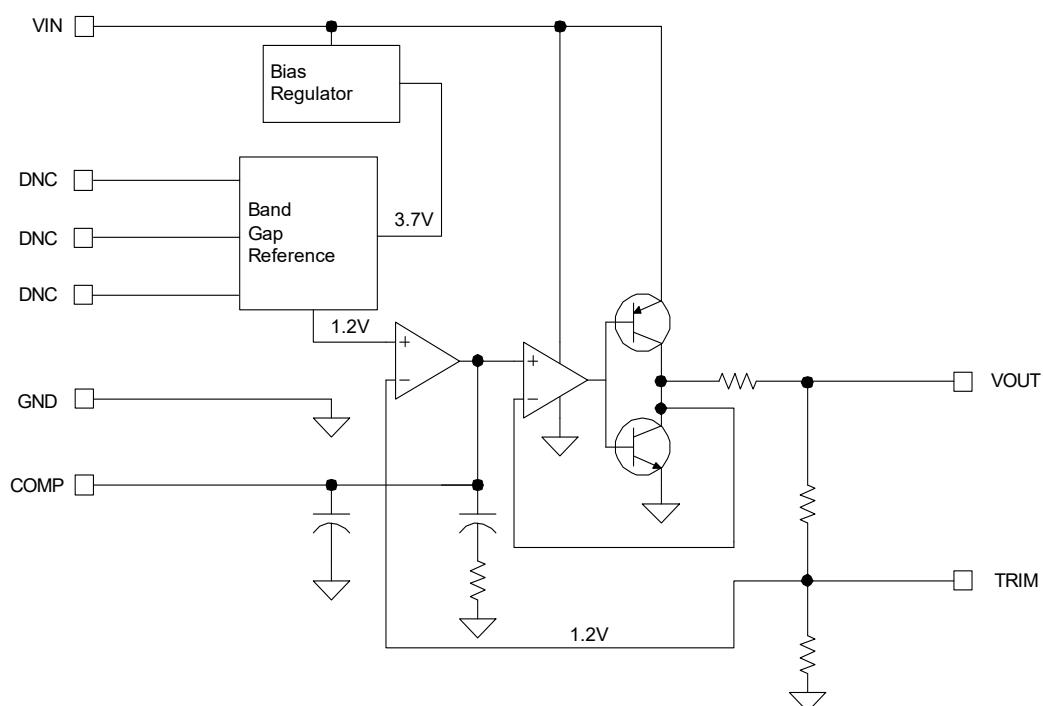


Figure 3. Functional Block Diagram

2. Pin Information

2.1 Pin Assignments

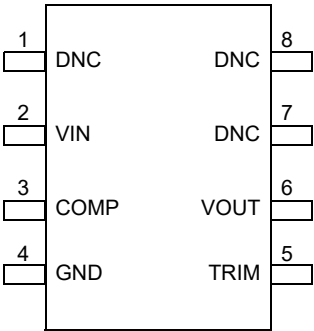


Figure 4. Pin Assignments - Top View

2.2 Pin Descriptions

Pin Number	Pin Name	ESD Circuit	Description
1, 7, 8	DNC	3	Do not connect. Internally terminated.
2	VIN	1	Input voltage connection
3	COMP	2	Compensation and noise reduction capacitor
4	GND	1	Ground connection.
5	TRIM	2	Voltage reference trim input
6	VOUT	2	Voltage reference output

Capacitively Triggered Clamp

ESD Circuit 1

Pins 3, 5, 6

ESD Circuit 2

ESD Circuit 3

3. Specifications

3.1 Absolute Maximum Ratings

Caution: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

Parameter	Minimum	Maximum	Unit
Max Voltage			
V_{IN} to GND	-0.5	+40	V
V_{OUT} to GND (10s)	-0.5	$V_{OUT} + 0.5$	V
Voltage on any Pin to Ground	-0.5	$+V_{OUT} + 0.5$	V
Voltage on DNC pins	No connections permitted to these pins		
Input Voltage Slew Rate (Max)	-	0.1	V/ μ s
Continuous Power Dissipation ($T_A = +125^\circ\text{C}$)	-	217	mW
Maximum Junction Temperature (T_{JMAX})	-	+150	$^\circ\text{C}$
Storage Temperature Range	-65	+150	$^\circ\text{C}$
Human Body Model (Tested per JS-001-2014)	-	3	kV
Machine Model (Tested per JESD22-A115-C)	-	200	V
Charged Device Model (Tested per JS-002-2014)	-	2	kV
Latch-up (Tested per JESD-78E; Class 2, Level A, at $+125^\circ\text{C}$)	-	± 100	mA

3.2 Recommended Operating Conditions

Parameter	Minimum	Maximum	Unit
V_{IN}	7.0	+30	V
Temperature Range	-55	+125	$^\circ\text{C}$

3.3 Thermal Information

Parameter	Package	Symbol	Conditions	Typical Value	Unit
Thermal Resistance	8 Ld SOIC Package	$\theta_{JA}^{[1]}$	Junction to ambient	110	$^\circ\text{C}/\text{W}$
		$\theta_{JC}^{[2]}$	Junction to case	60	$^\circ\text{C}/\text{W}$

1. θ_{JA} is measured with the component mounted on a high-effective thermal conductivity test board in free air. See [TB379](#) for details.

2. For θ_{JC} , the case temperature location is taken at the package top center.

3.4 Outgassing Testing

Specification (Tested per ASTM E 595, 1.5)	Value	Unit
Total Mass Lost ^[1]	0.06	%
Collected Volatile Condensable Material ^[1]	<0.01	%
Water Vapor Recovered	0.03	%

1. Results meet NASA low outgassing requirements of "Total Mass Lost" of <1% and "Collected Volatile Condensable Material" of <0.1%.

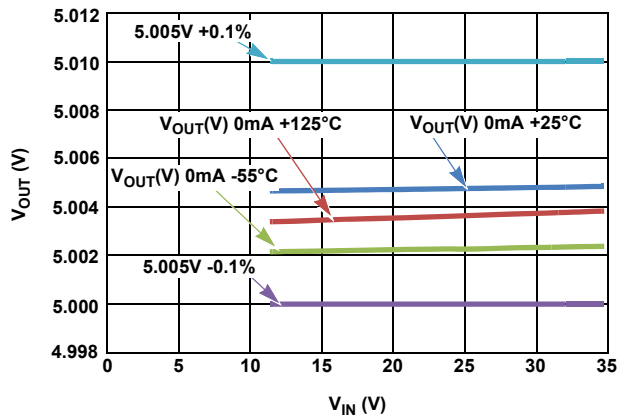
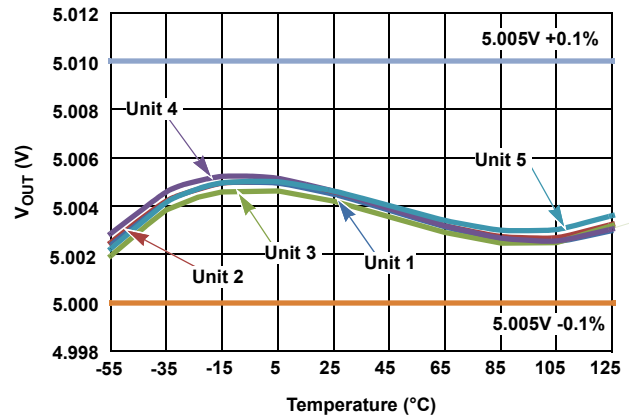
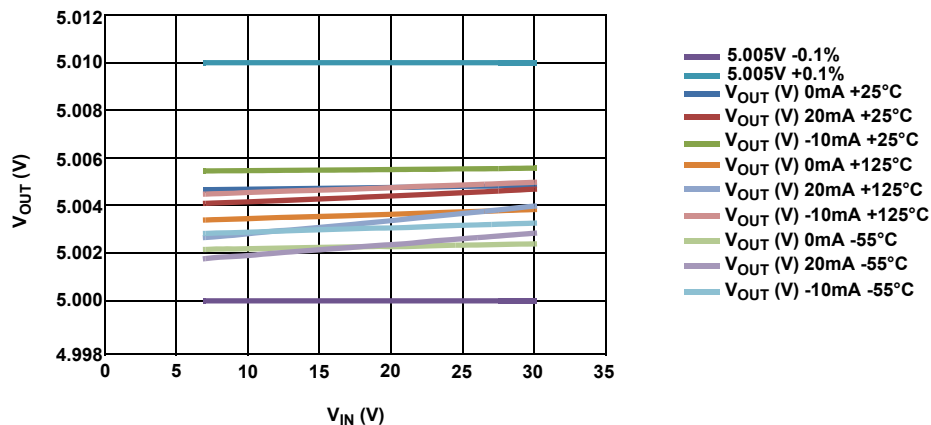
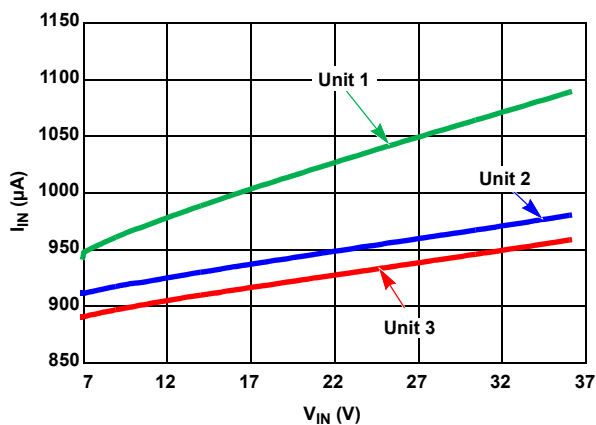
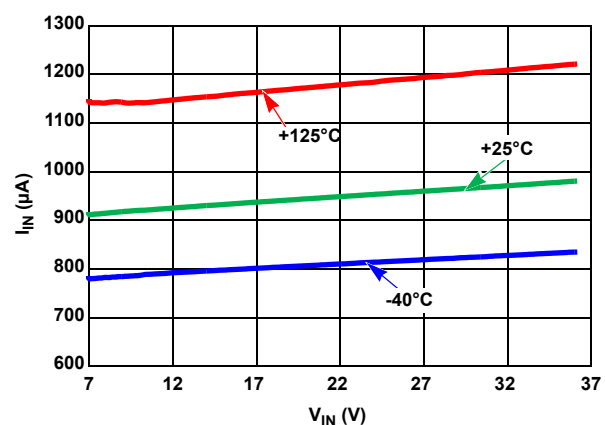
3.5 Electrical Specifications

$V_{IN} = 10V$, $I_{OUT} = 0mA$, $C_{OUT} = 0.1\mu F$, $COMP = 1nF$ unless otherwise specified. **Boldface limits apply across the operating temperature range, -55°C to +125°C by characterization with production testing at +25°C; over a total ionizing dose of 30krad(Si) at +25°C with exposure at a low dose rate of <10mrad(Si)/s (ISL71010BM30B50Z); or over a total ionizing dose of 50krad(Si) at +25°C with exposure at a low dose rate of <10mrad(Si)/s (ISL71010BM50B50Z).**

Parameter	Symbol	Conditions	Min ^[1]	Typ	Max ^[1]	Unit
Output Voltage	V_{OUT}	$V_{IN} = 10V$	-	5.0	-	V
V_{OUT} Accuracy ^[2]	V_{OA}	$V_{OUT} = 5.0V$, $T_A = +25^\circ C$	-0.05	-	+0.05	%
		$V_{OUT} = 5.0V$, $T_A = -55^\circ C$ to $+125^\circ C$	-0.15	-	+0.15	%
		$V_{OUT} = 5.0V$, $T_A = +25^\circ C$, 30krad(Si)	-0.15	-	+0.15	%
		$V_{OUT} = 5.0V$, $T_A = +25^\circ C$, 50krad(Si)	-0.20	-	+0.20	%
Output Voltage Temperature Coefficient ^[3]	TC V_{OUT}	-	-	-	10	ppm/°C
Input Voltage Range	V_{IN}	$V_{OUT} = 5.0V$	7	-	30	V
Supply Current	I_{IN}	-	-	0.930	1.33	mA
Line Regulation	$\Delta V_{OUT} / \Delta V_{IN}$	$V_{IN} = 7V$ to $30V$, $V_{OUT} = 5.0V$	-	8	20	ppm/V
Load Regulation	$\Delta V_{OUT} / \Delta I_{OUT}$	Sourcing: $0mA \leq I_{OUT} \leq 20mA$	-	2.5	17	ppm/mA
		Sinking: $-10mA \leq I_{OUT} \leq 0mA$	-	2.5	17	ppm/mA
Dropout Voltage ^[4]	V_D	$V_{OUT} = 5.0V$ at 10mA	-	1.1	1.7	V
Short-Circuit Current	I_{SC+}	$T_A = +25^\circ C$, V_{OUT} tied to GND	-	54	75	mA
Short-Circuit Current	I_{SC-}	$T_A = +25^\circ C$, V_{OUT} tied to V_{IN}	-100	-60	-	mA
Turn-On Settling Time	t_R	90% of final value, $C_L = 1.0\mu F$, $C_C = \text{Open}$	-	150	-	μs
Ripple Rejection		$f = 120Hz$	-	90	-	dB
Output Voltage Noise	e_{np-p}	$0.1Hz \leq f \leq 10Hz$, $V_{OUT} = 5.0V$	-	4.2	-	μV_{P-P}
Broadband Voltage Noise	V_n	$10Hz \leq f \leq 1kHz$, $V_{OUT} = 5.0V$	-	3.2	-	μV_{RMS}
Noise Voltage Density	e_n	$f = 1kHz$, $V_{OUT} = 5.0V$	-	100	-	nV/ $\sqrt{Hz}$
Long Term Stability	$\Delta V_{OUT} / \Delta t$	$T_A = +25^\circ C$	-	20	-	ppm

1. Compliance to datasheet limits is assured by one or more methods: production test, characterization, and/or design.
2. Post-reflow drift for the ISL71010B50 devices can exceed 100 μV to 1.0mV based on experimental results with devices on FR4 double sided boards. The system engineer must take this into account when considering the reference voltage after assembly.
3. Over the specified temperature range. Temperature coefficient is measured by the box method whereby the change in V_{OUT} is divided by the temperature range; in this case, -55°C to +125°C = +180°C. See [Specifying Temperature Coefficient \(Box Method\)](#) for more information.
4. Dropout Voltage is the minimum $V_{IN} - V_{OUT}$ differential voltage measured at the point where V_{OUT} drops 1mV from $V_{IN} = \text{Nominal}$ at $T_A = +25^\circ C$.

4. Typical Performance Curves

Figure 5. V_{OUT} Accuracy Over TemperatureFigure 6. 5.005V V_{OUT} Limits PlotFigure 7. V_{OUT} vs V_{IN} AT 0mA, 20mA, and -10mAFigure 8. I_{IN} vs V_{IN} , Three UnitsFigure 9. I_{IN} vs V_{IN} , Three Temperatures

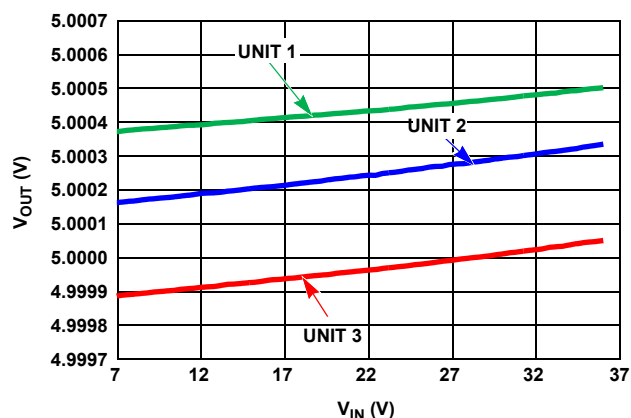


Figure 10. Line Regulation, Three Units

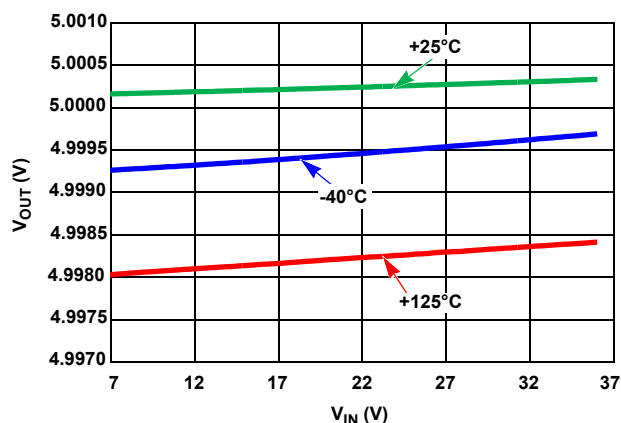


Figure 11. Line Regulation, Three Temperatures

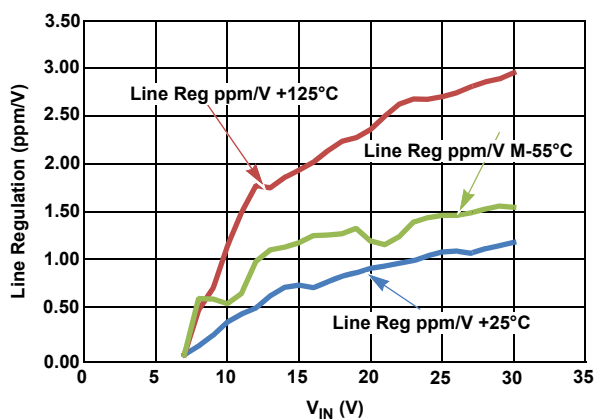
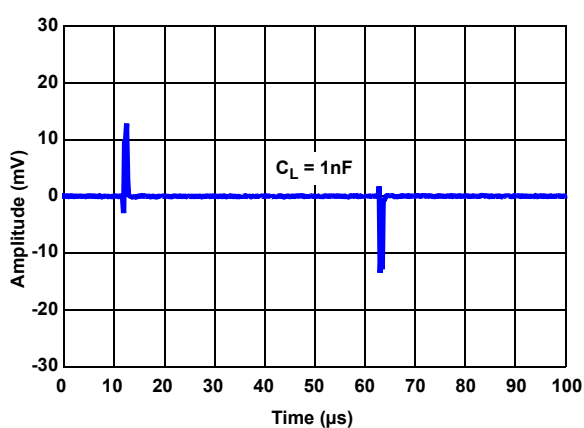
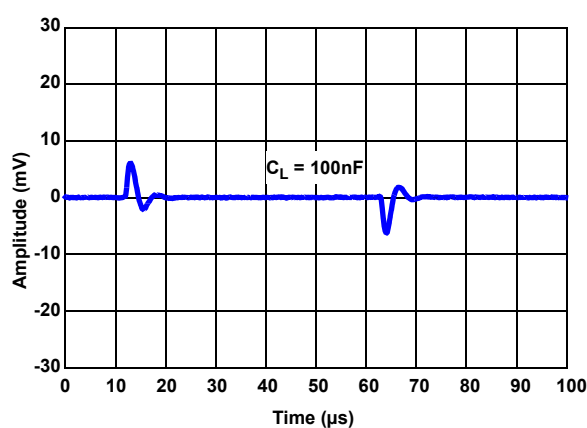


Figure 12. Line Regulation Over Temperature

Figure 13. Line Transient with 1nF LOAD
($\Delta V_{IN} = \pm 500\text{mV}$)Figure 14. Line Transient with 100nF LOAD
($\Delta V_{IN} = \pm 500\text{mV}$)

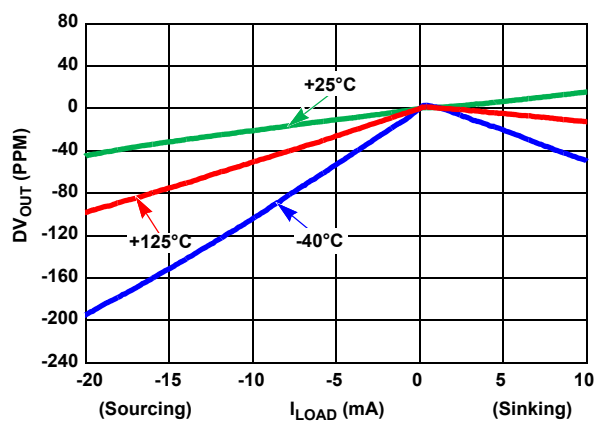


Figure 15. Load Regulation, Three Temperatures

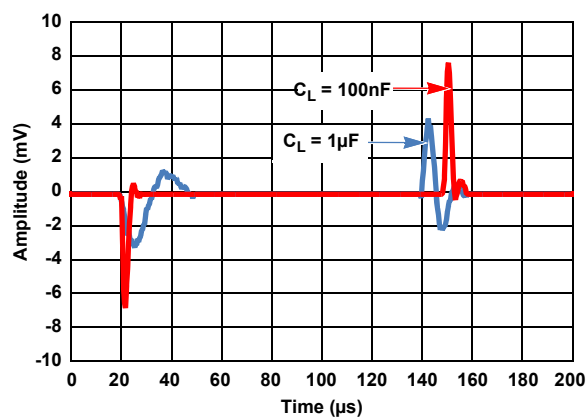
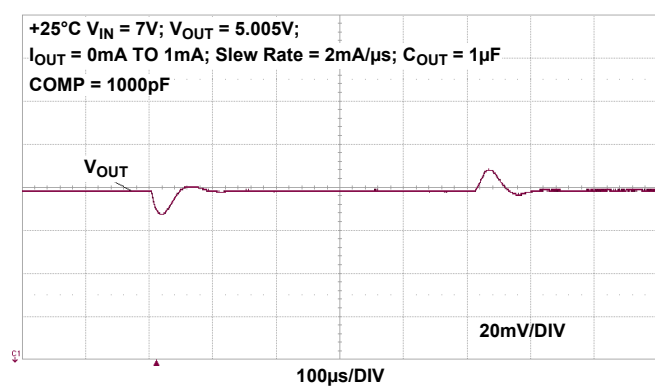
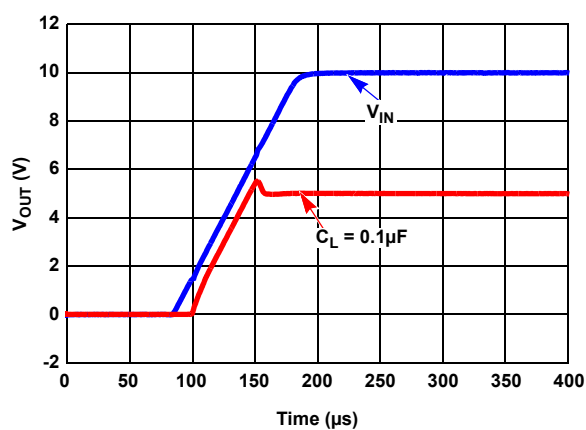
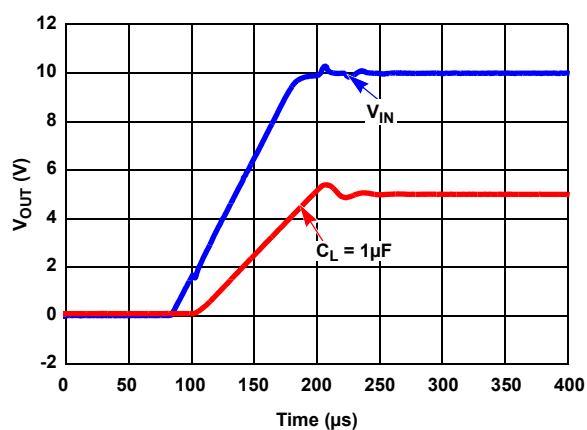
Figure 16. Load Transient ($\Delta I_{LOAD} = \pm 1\text{mA}$)

Figure 17. Load Transient (0mA to 1mA)

Figure 18. Turn-On Time with 0.1 μF Figure 19. Turn-On Time with 1 μF

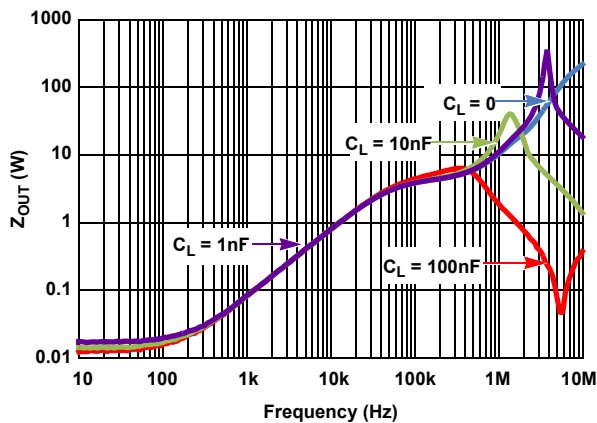


Figure 20. Z_{OUT} vs Frequency

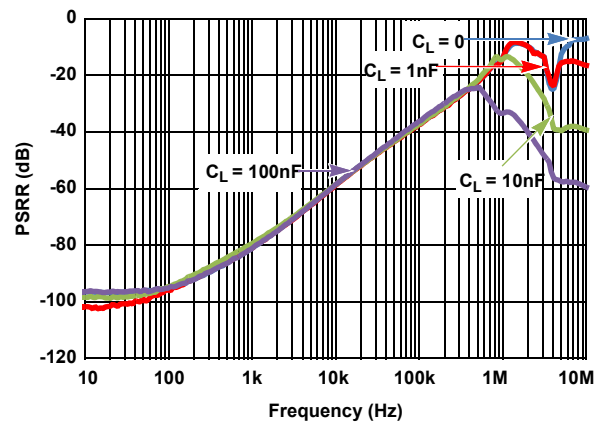


Figure 21. PSRR at Different Capacitive Loads

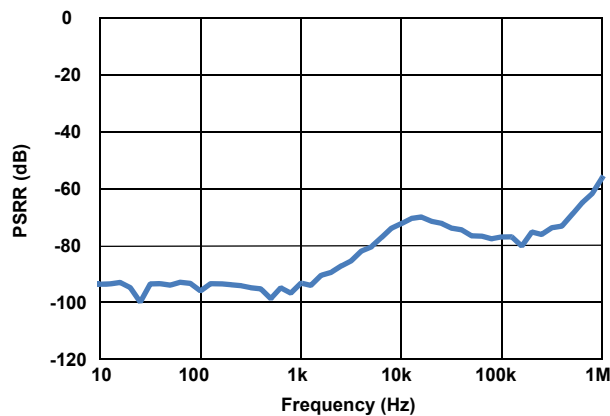


Figure 22. PSRR (+25°C, $V_{IN} = 7V$, $V_{OUT} = 5.005V$, $I_{OUT} = 0mA$, $C_{IN} = 0.1\mu F$, $C_{OUT} = 1.0\mu F$, $COMP = 1nF$, $V_{SIG} = 300mV_{P-P}$)

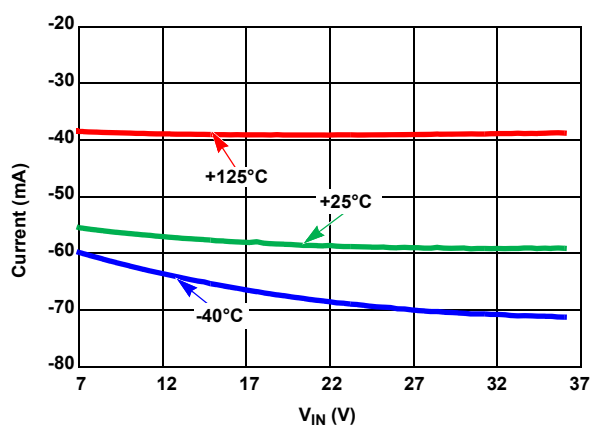


Figure 23. Short-Circuit to GND

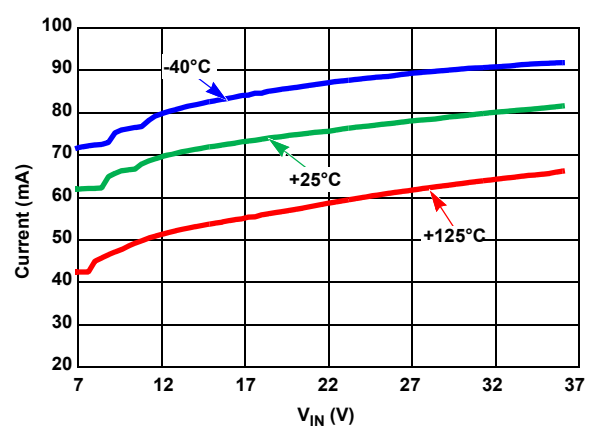


Figure 24. Short-Circuit to V_{IN}

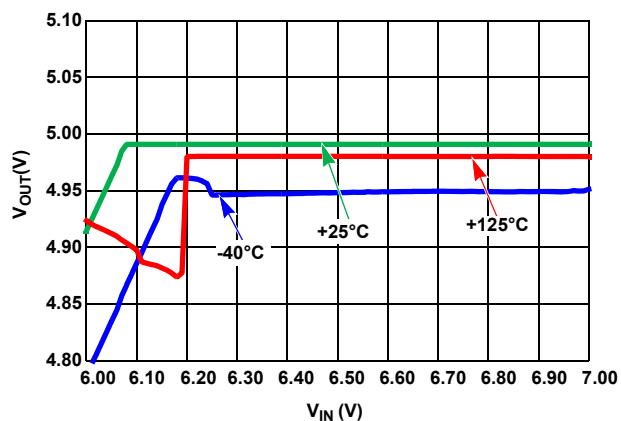


Figure 25. Dropout with -10mA Load

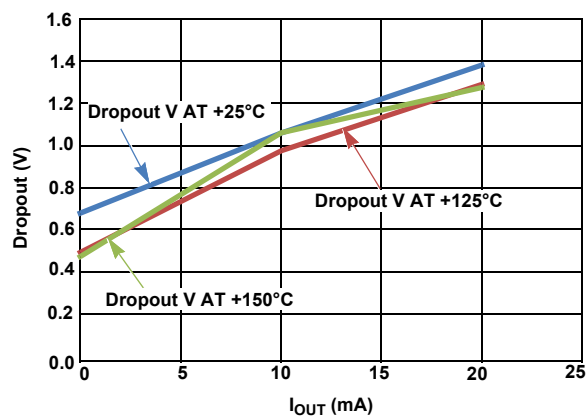
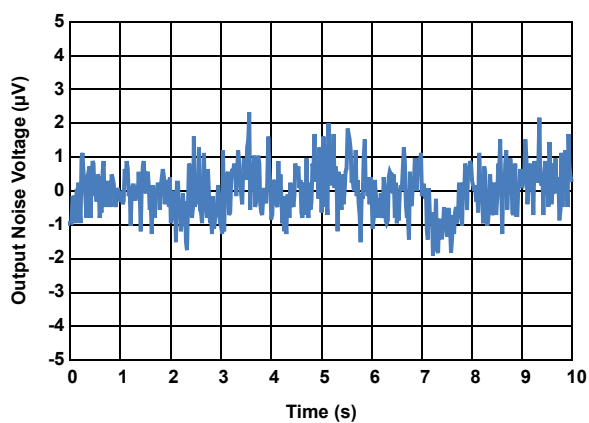
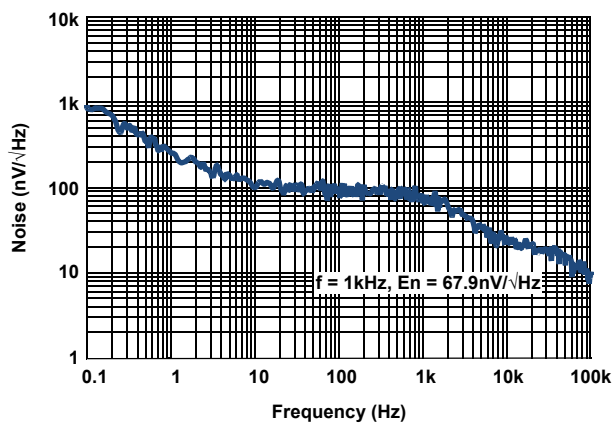


Figure 26. Dropout Voltage for 5.005V

Figure 27. V_{OUT} vs Noise, 0.1Hz to 10HzFigure 28. Noise Density vs Frequency ($V_{IN} = 7.1V$, $I_{OUT} = 0mA$, $C_{IN} = 0.1\mu F$, $C_{OUT} = 1\mu F$, $COMP = 1nF$)

5. Applications Information

5.1 Bandgap Precision Reference

The ISL71010B50 uses a bandgap architecture and special trimming circuitry to produce a temperature compensated, precision voltage reference with high input voltage capability and moderate output current drive.

5.2 Board Mounting Considerations

For applications requiring the highest accuracy, the board mounting location should be considered. The device uses a plastic SOIC package, which subjects the die to mild stresses when the Printed Circuit Board (PCB) is heated and cooled, which slightly changes the shape. Because of these die stresses, placing the device in areas subject to slight twisting can cause degradation of the reference voltage accuracy. It is normally best to place the device near the edge of a board, or on the shortest side, because the axis of bending is most limited in that location. Mounting the device in a cutout also minimizes flex. Obviously, mounting the device on flexprint or extremely thin PC material will likewise cause loss of reference accuracy.

5.3 Board Assembly Considerations

Some PCB assembly precautions are necessary. Normal output voltage shifts of 100 μ V can be expected with Pb-free reflow profiles or wave solder on multi-layer FR4 PCBs. Precautions should be taken to avoid excessive heat or extended exposure to high reflow or wave solder temperatures.

5.4 Noise Performance and Reduction

The output noise voltage in a 0.1Hz to 10Hz bandwidth is typically 4.2 μ V_{P-P} ($V_{OUT} = 5.0V$). The noise measurement is made with a bandpass filter. The filter is made of a 1-pole high-pass filter, with a corner frequency at 0.1Hz, and a 2-pole low-pass filter, with a corner frequency (3dB) at 9.9Hz, to create a filter with a 9.9Hz bandwidth. Noise in the 10Hz to 1kHz bandwidth is approximately 3.2 μ V_{RMS}, with 1 μ F capacitance on the output. This noise measurement is made with a 2 decade bandpass filter. The filter is made of a 1-pole high-pass filter with a corner frequency at 10Hz of the center frequency, and 1-pole low-pass filter with a corner frequency at 1kHz. Load capacitance up to 10 μ F can be added, but will result in only marginal improvements in output noise and transient response.

5.5 Turn-On Time

Normal turn-on time is typically 250 μ s. The circuit designer must take this into account when looking at power-up delays or sequencing.

5.6 Specifying Temperature Coefficient (Box Method)

The limits stated for temperature coefficient (Tempco) are governed by the method of measurement. The overwhelming standard for specifying the temperature drift of a reference is to measure the reference voltage at two temperatures. Divide the total variation ($V_{HIGH} - V_{LOW}$) by the temperature extremes of measurement ($T_{HIGH} - T_{LOW}$). The result is divided by the nominal reference voltage (at $T = +25^{\circ}C$) and multiplied by 10^6 to yield ppm/ $^{\circ}C$. This is the "Box" method for specifying temperature coefficient.

5.7 Output Voltage Adjustment

The output voltage can be adjusted above and below the factory-calibrated value using the trim terminal. The trim terminal is the negative feedback divider point of the output operational amplifier. The voltage at the TRIM pin is set at approximately 1.216V by the internal bandgap and amplifier circuitry of the voltage reference.

The suggested method to adjust the output is to connect a 1M Ω external resistor directly to the trim terminal and connect the other end to the wiper of a potentiometer that has a 100k Ω resistance and with outer terminals that connect to V_{OUT} and ground. If a 1M Ω resistor is connected to trim, the output adjust range will be $\pm 6.3mV$. The TRIM pin should not have any capacitor tied to its output. Also it is important to minimize the capacitance on the trim terminal during layout to preserve output amplifier stability. It is also best to connect the series resistor directly

to the trim terminal, to minimize that capacitance and also to minimize noise injection. Small trim adjustments do not disturb the factory-set temperature coefficient of the reference, but trimming near the extreme values can.

5.8 Output Stage

The output stage of the device has a push pull configuration with a high-side PNP and a low-side NPN. This helps the device to act as a source and sink. The device can source 20mA.

5.9 Use of COMP Capacitors

The reference can be compensated for the C_{OUT} capacitors used by adding a capacitor from COMP pin to GND. See [Table 1](#) for recommended values of the COMP capacitor.

Table 1. COMP Capacitor Recommended Values

C_{OUT} (μ F)	C_{COMP} (nF)
0.1	1
1	1
10	10

6. Radiation Tolerance

The ISL71010B50 is a radiation tolerant device for commercial space applications, Low Earth Orbit (LEO) applications, high altitude avionics, launch vehicles, and other harsh environments. This device's response to Total Ionizing Dose (TID) radiation effects and Single-Event Effects (SEE) has been measured, characterized, and reported in the following sections. The TID performance of the ISL71010B50 is not guaranteed through radiation lot acceptance testing. The ISL71010BM30B50 is radiation lot acceptance tested (RLAT) to 30krad(Si), and the ISL71010BM50B50 is RLAT to 50krad(Si).

6.1 Total Ionizing Dose (TID) Testing

6.1.1 Introduction

This test was conducted to determine the sensitivity of the part to the total dose environment. Testing was performed on two separate sample sets. For the first sample set, test downpoints were 0krad(Si), 10krad(Si), and 30krad(Si). The second sample set was irradiated to 50krad(Si).

Total dose testing was performed using a Hopewell Designs N40 panoramic ^{60}Co irradiator. The irradiations were performed at 10mrad(Si)/s. A PbAl box was used to shield the test fixture and devices under test against low energy secondary gamma radiation.

The characterization matrix of the first sample set consisted of four samples irradiated under bias and four samples irradiated with all pins grounded. The characterization matrix of the second sample set consisted of seven samples irradiated under bias and seven samples irradiated with all pins grounded. Four control units were used to ensure repeatable data. Two different wafers were used. The bias configuration is shown in [Figure 29](#).

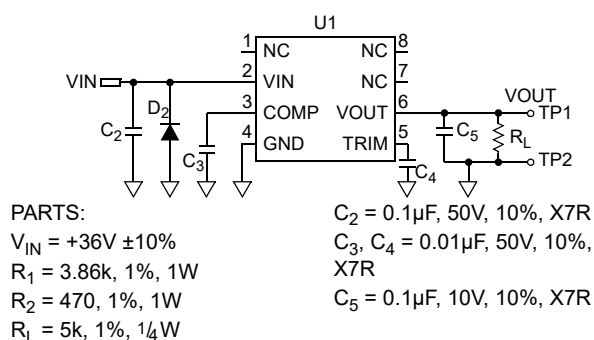


Figure 29. Irradiation Bias Configuration and Power Supply Sequencing for the ISL71010B50

All electrical testing was performed outside the irradiator using the production Automated Test Equipment (ATE), with data logging at each down point. Downpoint electrical testing was performed at room temperature.

6.1.2 Results

Table 2 summarizes the attributes data.

Table 2. ISL71010B50 Total Dose Test Attributes Data

Dose Rate (mrad(Si)/s)	Bias	Sample Size	Down Point	Pass ^[1]	Rejects
10	Figure 29	4	Pre-rad	4	0
			10krad(Si)	4	0
			30krad(Si)	4	0
		7	50krad(Si)	7	0
10	Grounded	4	Pre-rad	4	0
			10krad(Si)	4	0
			30krad(Si)	4	0
		7	50krad(Si)	7	0

1. A Pass indicates a device that passes all datasheet specification limits.

The plots in Figure 30 through Figure 35 show data for key parameters at all down points. The plots show the average as a function of total dose for each of the irradiation conditions. All parts showed excellent stability over irradiation.

Table 3 shows the average of the key parameters with respect to total dose in tabular form.

6.1.3 Data Plots

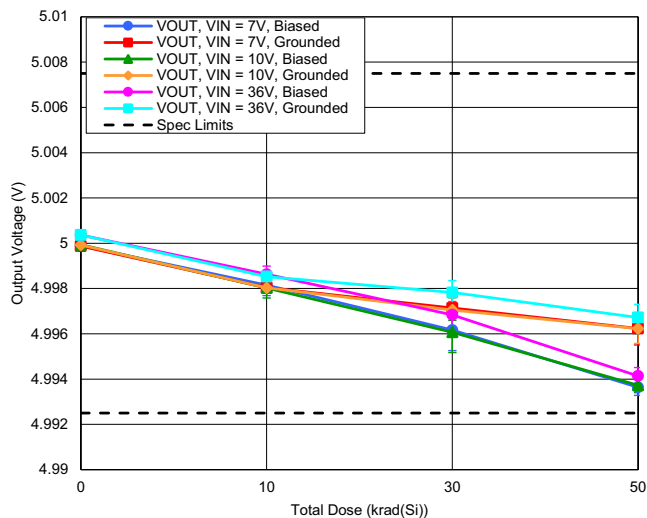


Figure 30. VREF Output Voltage vs TID

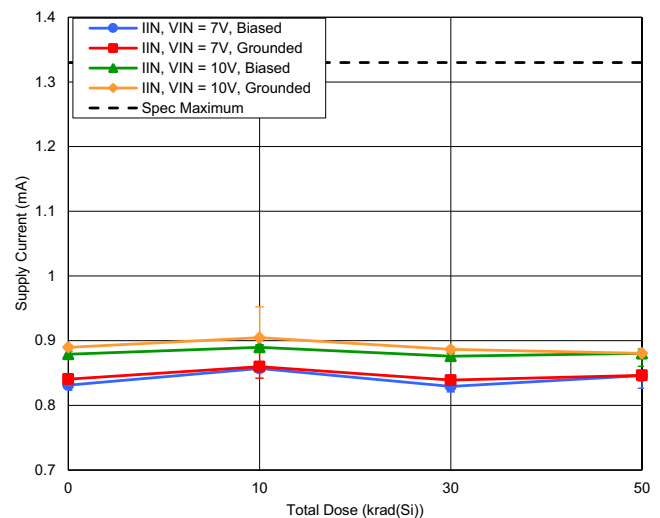


Figure 31. Supply Current vs TID

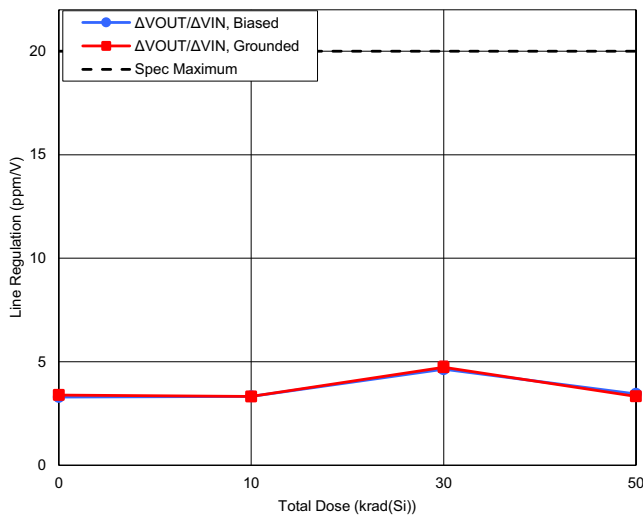


Figure 32. Line Regulation vs TID

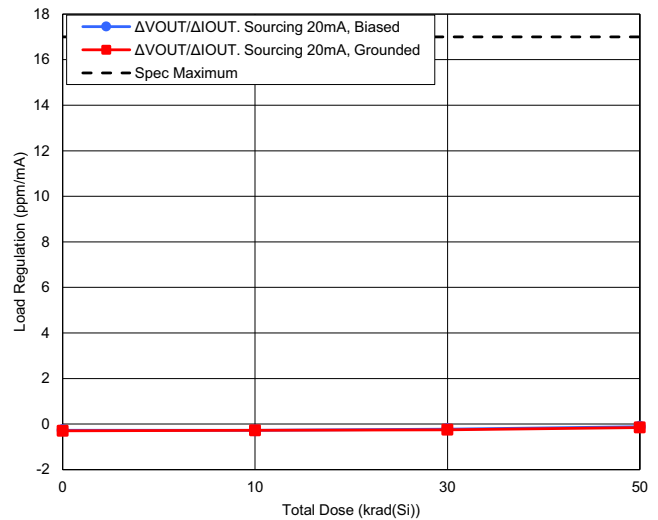


Figure 33. Load Regulation 20mA Sourcing vs TID

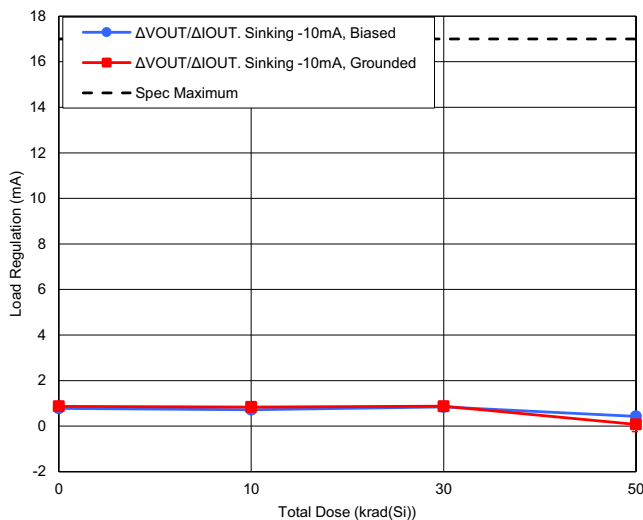


Figure 34. Load Regulation -10mA Sinking vs TID

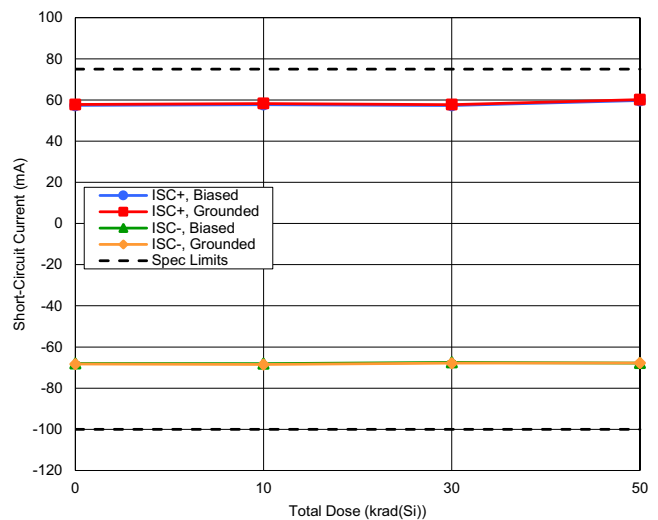


Figure 35. Short-Circuit Current vs TID

6.1.4 Conclusion

ATE characterization testing showed no rejects to the datasheet limits at all down points. Variables data for selected parameters is presented in Figure 30 through Figure 35. No differences between biased and unbiased irradiation were noted, and the part is not considered bias sensitive.

Table 3. ISL71010B50 Response of Key Parameters vs TID

Parameter	Symbol	Condition	Bias	0krad(Si)	10krad(Si)	30krad(Si)	50krad(Si)	Unit
Output Voltage	V_{OUT}	$V_{IN} = 10V$	Bias	4.999938	4.998027	4.996072	4.993725	V
			Grounded	4.999922	4.998032	4.997056	4.996227	
		$V_{IN} = 7V$	Bias	4.999885	4.998147	4.996166	4.993636	
			Grounded	4.999873	4.998045	4.997138	4.996235	
		$V_{IN} = 36V$	Bias	5.000362	4.99863	4.99684	4.994136	
			Grounded	5.000366	4.998528	4.997825	4.996719	

Table 3. ISL71010B50 Response of Key Parameters vs TID (Cont.)

Parameter	Symbol	Condition	Bias	0krad(Si)	10krad(Si)	30krad(Si)	50krad(Si)	Unit
Supply Current	I_{IN}	$V_{IN} = 7V$	Bias	0.831391	0.85709	0.829327	0.846038	mA
			Grounded	0.840696	0.859878	0.839203	0.84651	
		$V_{IN} = 10V$	Bias	0.879245	0.889788	0.876051	0.880307	
			Grounded	0.889907	0.90476	0.886532	0.880486	
Line Regulation	$\Delta V_{OUT}/\Delta V_{IN}$	$V_{IN} = 4V$ to $30V$, $V_{OUT} = 2.5V$	Bias	3.295899	3.327616	4.641101	3.446307	ppm/V
			Grounded	3.395929	3.326168	4.734789	3.332438	
Load Regulation	$\Delta V_{OUT}/\Delta I_{OUT}$	20mA Sourcing	Bias	-0.27145	-0.27352	-0.22263	-0.11585	ppm/mA
			Grounded	-0.29523	-0.27458	-0.25169	-0.15318	
		-10mA Sinking	Bias	0.78336	0.720432	0.843916	0.428049	
			Grounded	0.86987	0.840889	0.877108	0.076316	
Short-Circuit Current	I_{SC+}	$V_{OUT} = GND$	Bias	57.37025	57.72532	57.32021	59.76282	mA
			Grounded	57.80417	58.30301	57.73128	60.18774	
	I_{SC-}	$V_{OUT} = V_{IN}$	Bias	-68.0334	-68.0907	-67.4924	-67.7959	
			Grounded	-68.2972	-68.4802	-67.8589	-67.7662	

6.2 Single Event Effects Testing

6.2.1 Introduction

The intense heavy ion environment encountered in space applications can cause a variety of Single-Event Effects (SEE). SEE can lead to system-level performance issues including disruption, degradation, and destruction. For predictable and reliable space system operation, individual electronic components should be characterized to determine their SEE response. The following is a summary of the ISL71010B50 SEE testing.

6.2.2 SEE Test Setup

Testing was performed at the Texas A&M University (TAMU) Cyclotron Institute heavy ion facility.

A schematic of the ISL71010B50 SEE test circuit is shown in [Figure 40](#). The test circuit is configured to accept an input voltage from 7V to 30V and generate the 5.0V nominal output voltage. The output current of the reference was adjusted using fixed load resistors on a test board. The output capacitor, C_4 , and the compensation capacitor C_2 were 0.1 μ F and 10nF, respectively.

Digital multimeters were used to monitor input voltage (V_{IN}), output voltage (V_{OUT}), and input current (I_{IN}). A LeCroy waveRunner digital oscilloscope was used to monitor, capture, and store key signal waveforms. The scope was configured to trigger with V_{OUT} signal levels of ± 50 mV.

6.2.3 SEB Testing Results

For the SEB tests, conditions were selected to maximize the electrical and thermal stresses on the Device Under Test (DUT), thus insuring worst-case conditions. The input voltage (V_{IN}) was initially set to 35V and then increased in 1V increments. The capacitors were set to $C_{OUT} = 0.1\mu$ F and $C_{COMP} = 1$ nF. SEB testing was conducted with the ISL71010B25. Output current (I_{OUT}) was set to 20mA which is the maximum recommended current rating for load regulation of the device. Case temperature was maintained at +125°C by controlling the current flowing into a resistor heater bonded to the underside of the DUT. Four DUTs were irradiated with Ag ions at a normal incident angle, resulting in an effective LET of 43MeV•cm²/mg.

The failure criterion for destructive SEE was an increase in operating input current (I_{IN}) greater than 5% measured at 20mA output current. I_{IN} is defined as the total current drawn by the device. Failed devices were not further irradiated.

From a design perspective, the ISL71010B25 and the ISL71010B50 are exactly the same in silicon. The output voltages, even though they are different values, are produced the same way and trimmed through a resistor ladder network. All the parts are built in the same process and are functionally equivalent. Therefore, the ISL71010B25 SEB results are applicable to the ISL71010B50.

Four parts passed irradiation to 1×10^7 ions/cm² with 43MeV•cm²/mg at 39V and +125°C case temperature.

6.2.4 Single Event Transient (SET) Testing

SET testing was done on four samples of the ISL71010B50, which were irradiated at room temperature at LETs of 2.7MeV•cm²/mg and 28MeV•cm²/mg to observe SET performance. Samples were separately tested to V_{IN} of 7V and 30V. The parts were configured with a 0.1μF output capacitor, 10nF compensation capacitor, and a 20mA load current to set up the worst conditions for negative going transients. Table 4 shows the SET summary giving the cross section for each input voltage and LET level.

Figure 36 through Figure 39 represent output waveform responses of the DUTs at the respective bias conditions and LET levels. The plots are composites of all the transients captured on the scope.

The SET exhibited by the ISL71010B50 fall into two basic categories; fast negative spike and slow negative ramp. The fast spikes can be as large as 500mV for LET 28 and $V_{IN} = 30V$. Under the same conditions, the slow (20μs) negative ramp can reach 300mV. The slow ramp disturbances can take significantly over 160μs to recover. Even at LET = 8.5MeV•cm²/mg (Figure 36 and Figure 37), there are SET of approximately 200mV.

Table 4. SET Summary of Fully Functional ISL71010B50

Supply Voltage (V) ^[1]	LET (MeV•cm ² /mg)	Fluence (Particles/cm ²)	Events (±50mV)	Events CS (cm ²)
7	8.5	8.00E+06	375	4.69E-05
30	8.5	8.00E+06	442	5.53E-05
7	28	8.00E+06	743	9.29E-05
30	28	8.00E+06	1073	1.34E-04

1. Samples at 7.0V and 30V input voltage. trigger level for the output voltage SET to ±50mV.

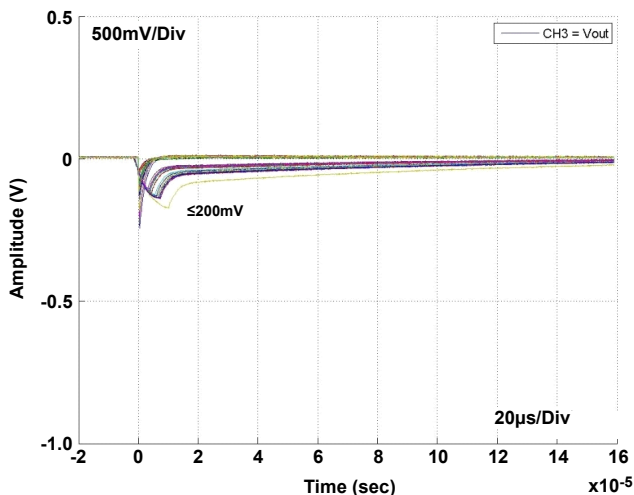


Figure 36. Composite SET Plot for ISL71010B50 at LET 8.5 $V_{IN} = 7V$, $I_{OUT} = 20mA$, $C_{OUT} = 0.1\mu F$, $C_{COMP} = 10nF$

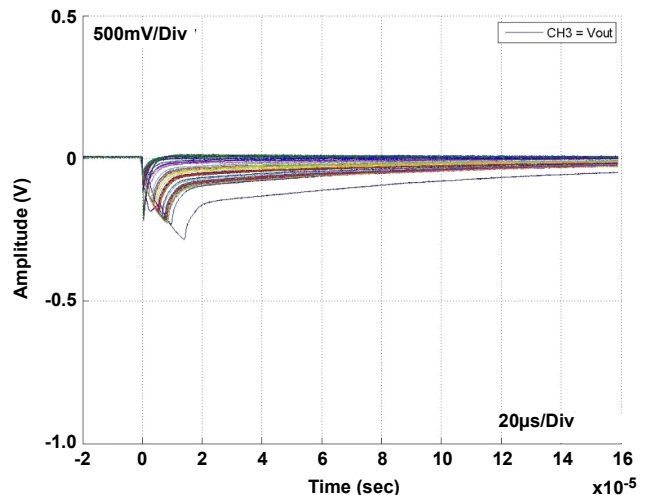


Figure 37. Composite SET Plot for ISL71010B50 at LET 8.5 $V_{IN} = 30V$, $I_{OUT} = 20mA$, $C_{OUT} = 0.1\mu F$, $C_{COMP} = 10nF$

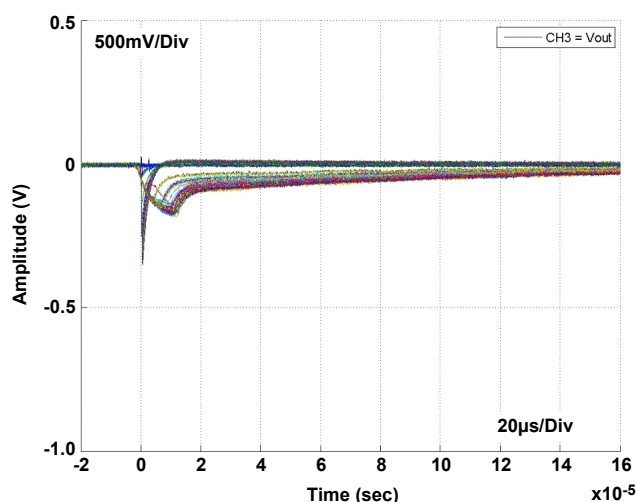


Figure 38. Composite SET Plot for ISL71010B50 at LET 28 $V_{IN} = 7V$, $I_{OUT} = 20mA$, $C_{OUT} = 0.1\mu F$, $C_{COMP} = 10nF$

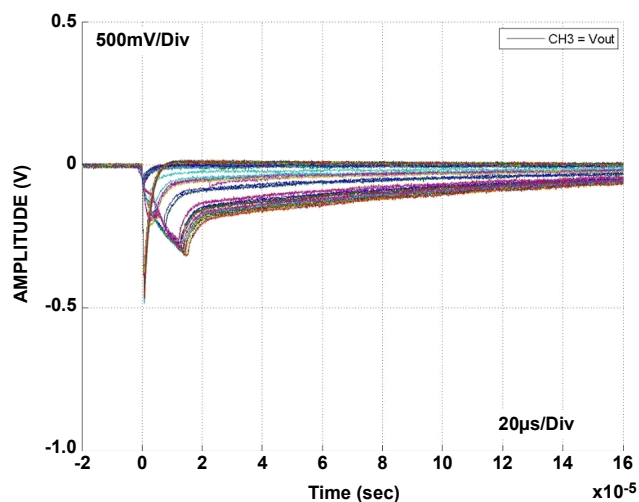


Figure 39. Composite SET Plot for ISL71010B50 at LET 28 $V_{IN} = 30V$, $I_{OUT} = 20mA$, $C_{OUT} = 0.1\mu F$, $C_{COMP} = 10nF$

7. Conclusion

SEE testing has demonstrated that the ISL71010B50 is not susceptible to Single Event Burnout (SEB) at an LET of $43MeV \cdot cm^2/mg$ with an input voltage of 39V and a load current of 20mA. This represents conditions that are over 30% above the recommended input voltage of 30V and 100% of the load regulation drive capability of the IC (20mA).

SET testing demonstrated that all transients are negative and the higher the LET level the greater the magnitude of the negative transient. At $LET = 28MeV \cdot cm^2/mg$ and $V_{IN} = 30V$ with $C_{OUT} = 0.10\mu F$, showed a 500mV fast negative transient and a 300mV slow (20us) negative transient during an SET event. The slow transient can take over 160µs to recovery. At $LET = 8.5MeV \cdot cm^2/mg$ there are SET of approximately 200mV.

A larger C_{OUT} capacitance value will suppress the SET magnitude but the SET disturbance duration will stretch out. Capacitor selection represents a compromise between SET magnitude and recovery duration.

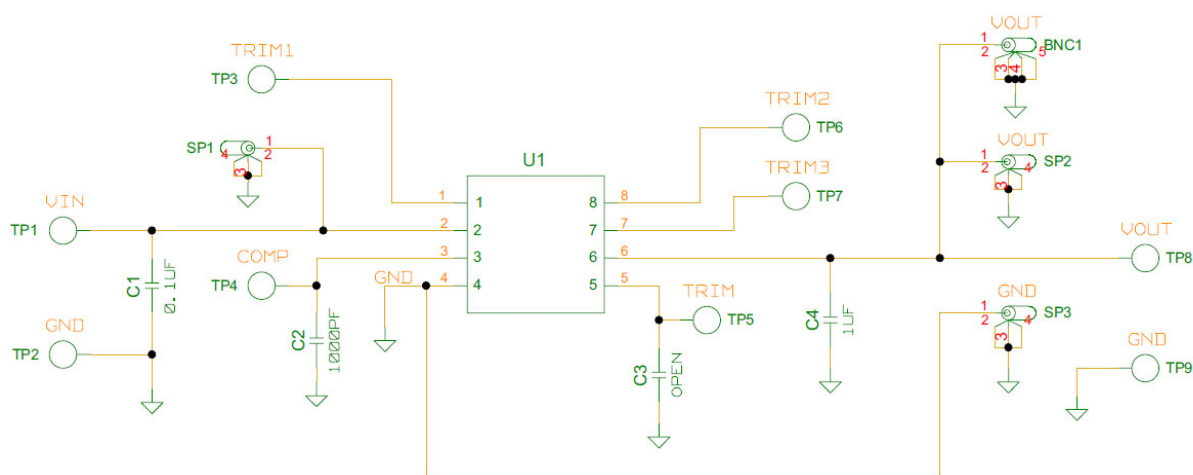


Figure 40. SEE Testing Schematic for the ISL71010B50

8. Package Outline Drawing

The package outline drawing is located at the end of this document and is accessible from the Renesas website. The package information is the most current data available and is subject to change without revision of this document.

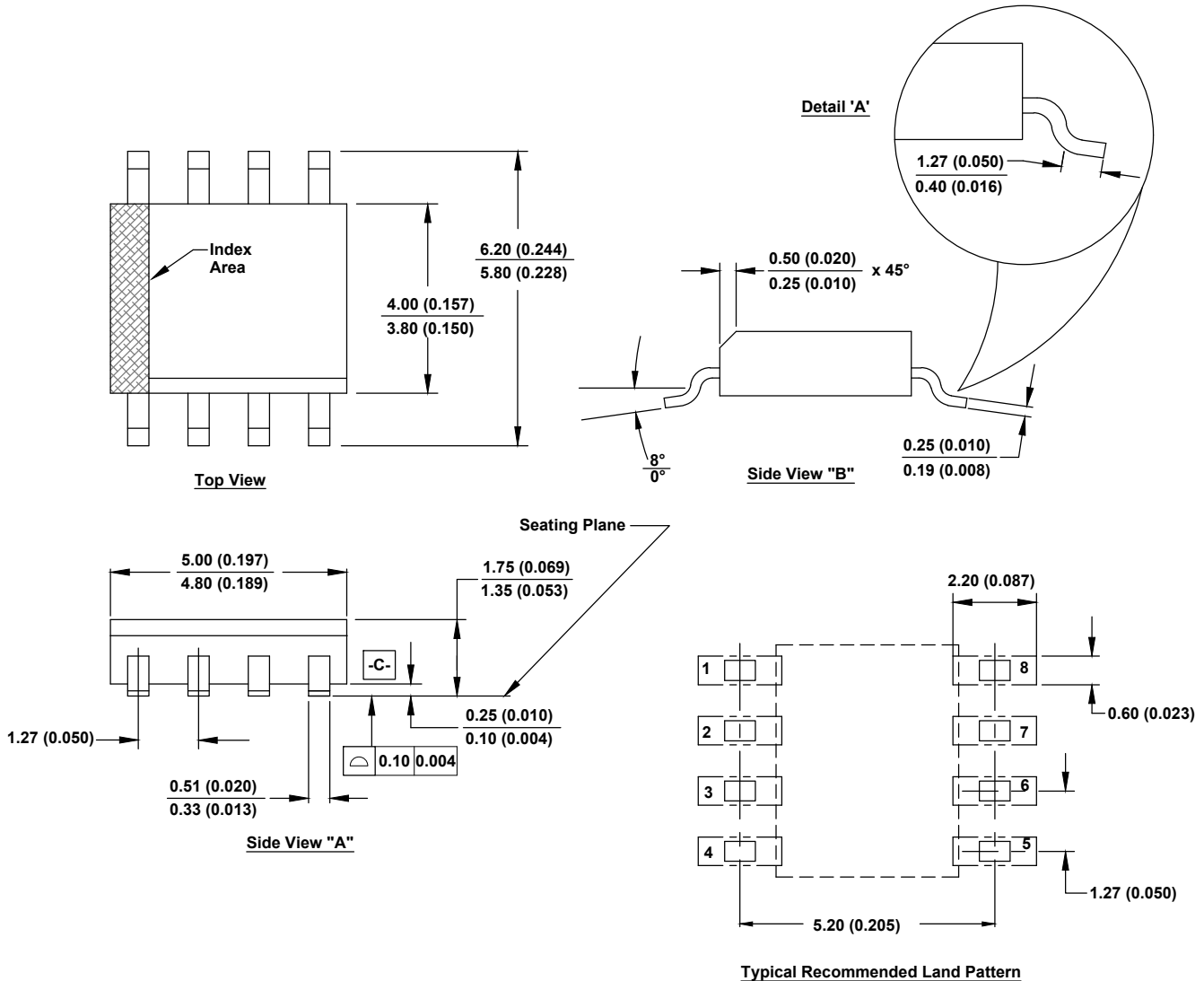
9. Ordering Information

Part Number ^[1] [2]	Part Marking	Radiation Lot Acceptance Testing	V _{OUT} Option (V)	Accuracy (%) T _A = 25°C	Tempco (ppm/°C)	Package Description ^[3] (RoHS Compliant)	Pkg. Dwg. #	Carrier Type ^[4]	Temp Range
ISL71010BMB50Z	71010 BMZ50	N/A	5.0	±0.05	10	8 Ld SOIC	M8.15	Tube	-55 to +125°C
ISL71010BMB50Z-TK								Reel, 1k	
ISL71010BM30B50Z	71010 BMZ50	30krad(Si)	5.0	±0.15	10	8 Ld SOIC	M8.15	Tube	-55 to +125°C
ISL71010BM30B50Z-TK								Reel, 1k	
ISL71010BM50B50Z	71010 BMZ50	50krad(Si)	5.0	±0.20	10	8 Ld SOIC	M8.15	Tube	-55 to +125°C
ISL71010BM50B50Z-TK								Reel, 1k	
ISL71010BM50EV1Z	Evaluation Board								

- These Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials and NiPdAu-Ag plate -e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J-STD-020.
- For Moisture Sensitivity Level (MSL), see the [ISL71010B50](#) device page. For more information about MSL, refer to [TB363](#).
- For the Pb-Free Reflow Profile, see [TB493](#).
- See [TB347](#) for details about reel specifications.

10. Revision History

Rev.	Date	Description
1.02	Sep 18, 2025	Added Qualification Feature bullet.
1.01	Aug 12, 2025	Applied latest template. Updated Radiation bullets. Updated Radiation Tolerance sections. Updated POD M8.15 to the latest version. Updated Ordering Information table.
1.00	Apr 12, 2018	Added Outgassing Feature bullet. Updated Ordering information by adding -TK part to table and updated Note 1. Added Outgassing specification information. Removed About Intersil and updated disclaimer.
0.00	Sep 29, 2017	Initial release



Notes:

1. Dimensioning and tolerancing conform to ASME Y14.5M-1994.
2. Package length does not include mold flash, protrusion or gate burrs. Mold flash, protrusion and gate burrs shall not exceed 0.15mm (0.006 inch) per side.
3. Package width does not include interlead flash or protrusions. Interlead flash and protrusions shall not exceed 0.25mm (0.010 inch) per side.
4. The chamfer on the body is optional. If it is not present, a visual index feature must be located within the crosshatched area.
5. Terminal numbers are shown for reference only.
6. The lead width as measured 0.36mm (0.014 inch) or greater above the seating plane, shall not exceed a maximum value of 0.61mm (0.024 inch).
7. Controlling dimension: MILLIMETER. Converted inch dimension are not necessarily exact.
8. This outline conforms to JEDEC publication MS-012-AA ISSUE C.

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